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of

Sheet

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Complete if Known				
Application Number 10/509,354				
Filing Date September 27, 2004				
First Named Inventor	Nick Zakhleniuk			
Art Unit	N/A			
Examiner Name Not Yet Assigned				
Attorney Docket Number	aber BTW-087US			

U.S. PATENT DOCUMENTS						
Examiner Initiats*	0:10	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Cotumns, Lines, Where Relevant Passages or Relevant Figures Appear	
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		NON PATENT LITERATURE DOCUMENTS	
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²
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S	TATEMENT E	3Y /	APPLICANT	First Named Inventor	Nick Zakhleniuk	
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	(Use as many sheets as necessary)			Examiner Name	Not Yet Assigned	
Sheet	2	of	2	Attorney Docket Number	BTW-087US	

		NON PATENT LITERATURE DOCUMENTS				
Examiner Initials	Cite Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher and/or country where published.					
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